

## UNITED STATES DEPARTMENT OF COMMERCE Pat nt and Trademark Office

Address: COMMISSIONER OF PATENTS AND TRADEMARKS

Washington, D.C. 20231

APPLICATION NO.	FILING DATE	FIRST NAMED INVEN	ITOR		ATT	ATTORNEY DOCKET NO.	
09/250,400 0	2/16/99	YAMASHITA		ΙΥI	35.C	35.C13319	
005514		MMC2/0830	$\neg$		EXAMINER		
FITZPATRICK CELLA HARPER & SCINTO 30 ROCKEFELLER PLAZA				RAMSE	Y,K		
EW YORK NY 10:				AF	TUNIT	PAPER NUMBER	
				2879			
			٠	DATE N	MAILED: 08/3	80/00	

Please find below and/or attached an Office communication concerning this application or proceeding.

**Commissioner of Patents and Trademarks** 

## Office Action Summary

Application No.

Applicant(s) 09/250,400

Examiner

Group Art Unit Kenneth J. Ramsev

Yamashita et al



	Remedi J. Ramsey	2879
X Responsive to communication(s) filed on 5/15/00 (IDS)		
☐ This action is <b>FINAL</b> .		
☐ Since this application is in condition for allowance excel in accordance with the practice under <i>Ex parte Quayle</i> ,	ot for formal matters, prosecutio 1935 C.D. 11; 453 O.G. 213.	n as to the merits is closed
A shortened statutory period for response to this action is is longer, from the mailing date of this communication. Fai application to become abandoned. (35 U.S.C. § 133). Ext 37 CFR 1.136(a).	set to expire3 month(	for roomanne will as a star
Disposition of Claims		
X Claim(s) <u>1-17</u>	is/are p	ending in the application.
Of the above, claim(s)		
Claim(s)	is	are allowed.
	ie	
Claim(s)	is/	are objected to
☐ Claims	are subject to restriction	
Application Papers	are subject to restriction	or election requirement.
☐ See the attached Notice of Draftsperson's Patent Dra	wing Review PTO-049	
☐ The drawing(s) filed on is/are ob		
☐ The proposed drawing correction, filed on		isapproved.
☐ The specification is objected to by the Examiner.	isapprovedd	isappioved.
☐ The oath or declaration is objected to by the Examine	г.	
Priority under 35 U.S.C. § 119		
Acknowledgement is made of a claim for foreign prior	ity under 35 U.S.C. § 119(a)-(d)	
	s of the priority documents have	· · been
🔀 received.		
received in Application No. (Series Code/Serial I	Number)	
$\square$ received in this national stage application from t	the International Bureau (PCT Ru	le 17.2(a)).
*Certified copies not received:		<u> </u>
<ul> <li>Acknowledgement is made of a claim for domestic pri</li> </ul>	ority under 35 U.S.C. § 119(e).	
Attachment(s)		
Notice of References Cited, PTO-892		
Information Disclosure Statement(s), PTO-1449, Paper	No(s)	
☐ Interview Summary, PTO-413		
Notice of Draftsperson's Patent Drawing Review, PTO	-948	
☐ Notice of Informal Patent Application, PTO-152		
SEE OFFICE ACTION OI	N THE FOLLOWING PAGES	

Art Unit: 2879

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless --

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- (e) the invention was described in a patent granted on an application for patent by another filed in the United States before the invention thereof by the applicant for patent, or on an international application by another who has fulfilled the requirements of paragraphs (1), (2), and (4) of section 371(c) of this title before the invention thereof by the applicant for patent.

Claims 1-5 and 11-17 rejected under 35 U.S.C. 102(e) as being anticipated by Kawade et al, US patent 6,034,478. Column 11, line 32 through column 12, line 41 discloses energization forming in an atmosphere comprising a gas that promotes the cohesion of the electroconductive film while heating the film by resistance. The cohesion promoting gas atmosphere comprises H<sub>2</sub>, CO or methane. The electron-emitting devices so formed are provided as an electron source of an image forming device (figure 8). As to claims 11 and 12 a palladium oxide film is formed by the process disclosed at column 25, lines 1-8. Thus claims 1-5 and 11-17 are anticipated.

Claims 1-5 and 11-17 are rejected under 35 U.S.C. 102(b) as being anticipated by Kawade et al, Japanese patent application no. Hei 09-298029. Paragraph [0086] through paragraph [0090] of Kawade et al discloses energization forming of a palladium oxide film in an atmosphere comprising a gas that promotes cohesion of the electroconductive film while heating the film by resistance. The cohesion promoting gas comprises H<sub>2</sub>, CO, or methane; see paragraph [0069]. The electron-emitting devices so formed are provided as an electron source of an image forming device (figure 12). Thus claims 1-5 and 11-15 are anticipated.

Application/Control Number: 09/250,400

Art Unit: 2879

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in

rejections set forth in this Office action:

section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are

such that the subject matter as a whole would have been obvious at the time the invention was made to a person

having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the

manner in which the invention was made.

Claims 9-12 are rejected under 35 U.S.C. 103(a) as being unpatentable over Kawade et al,

JP patent application no. Hei 09-298029 or US patent 6,034,478, in view of Talko et al EP patent

769,796. To form the palladium oxide film of Kawade et al by the ink jet droplet method of

Talko et al, column 32, lines 30-41, would have been obvious to one of ordinary skill in the art

since accurate placement of the film is possible.

Claims 6-8 are rejected under 35 U.S.C. 103(a) as being unpatentable over Kawade et al

and Talko et al as applied to claim 9 above, and further in view of Ono et al, hei 08-31311. While

Kawade et al relies upon resistance heating of the oxide film it is also obvious that the film should

be heated between 20 and 400 degrees C since that is the temperature set forth in Ono et al

paragraph [0066] for reducing oxide films in a reducing gas. Use of heating by maintaining the

substrate at 50-100 degrees, claim 8, would have been obvious since this would stabilized the

reduction process.

Any inquiry concerning this communication should be directed to

Kenneth J. Ramsey, (703)308-2324 (voice), (703) 308-7382 (fax).

**KJR** 

August 25, 2000

Kenneth J. Ramsey

meth / Rawsey

Page 3

**Primary Examiner**